KDV273UL

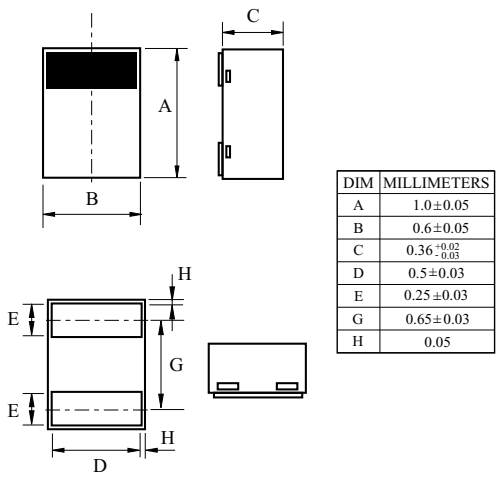
VARIABLE CAPACITANCE DIODE
SILICON EPITAXIAL PLANAR DIODE

VCO FOR UHF/VHF BAND.

TENTATIVE

FEATURES

- High Capacitance Ratio : C_{1V}/C_{4V} =2.0(Typ.)
- Low Series Resistance : r_s=0.39 Ω (Typ.)



DIM	MILLIMETERS
A	1.0±0.05
B	0.6±0.05
C	$0.36^{+0.02}_{-0.03}$
D	0.5±0.03
E	0.25±0.03
G	0.65±0.03
H	0.05

1. ANODE
2. CATHODE

ULP-2

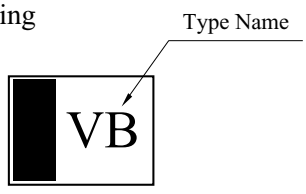
MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	V_R	10	V
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55～150	℃

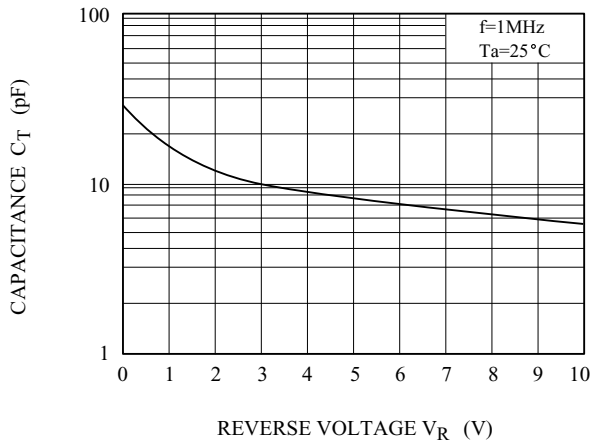
ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Voltage	V_R	I_R=1μA	10	-	-	V
Reverse Current	I_R	V_R=10V	-	-	10	nA
Capacitance	C_{1V}	V_R=1V, f=1MHz	15	16	17	pF
	C_{4V}	V_R=4V, f=1MHz	7.3	8.0	8.7	
Capacitance Ratio	K	-	1.8	2.0	-	
Series Resistance	r_S	V_R=1V, f=470MHz	-	0.39	0.5	Ω

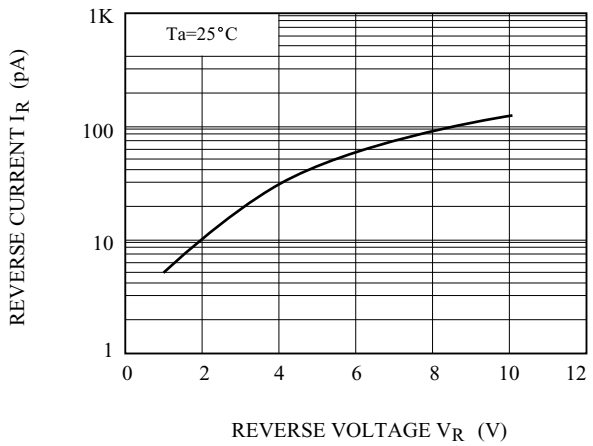
Marking



C_T - V_R


100
10
1
f=1MHz
Ta=25°C
CAPACITANCE C_T (pF)
0 1 2 3 4 5 6 7 8 9 10
REVERSE VOLTAGE V_R (V)

I_R - V_R


1K
100
10
1
Ta=25°C
REVERSE CURRENT I_R (pA)
0 2 4 6 8 10 12
REVERSE VOLTAGE V_R (V)